

consisting of $C(CH_2OH)_3$, a sugar unit, SiR_3 wherein R is a polar group selected from the group consisting of:

5 65. The method according to Claim 34, wherein the composition further comprises a co-solvent.

10 66. The method according to Claim 34, further comprising the step of selectively etching the wafer, wherein said step of selectively etching the wafer occurs subsequent to step (c) but prior to step (d).

15 67. A process of forming integrated circuits comprising the steps of:

 (a) inserting at least one wafer into an integrated microelectronics process device (IMPD); then

20 (b) contacting the at least one wafer with a first composition comprising a component selected from the group consisting of at least one polymeric material, at least one polymeric precursor, and at least one monomer, and mixtures thereof, to deposit the component on the substrate and form a coating thereon; then

25 (c) imagewise exposing the coating to radiation such that exposed and unexposed coating portions are formed; then

 (d) subjecting the coating to a second composition comprising carbon dioxide such that either one of the exposed or the unexposed coating portions are removed from the at least one wafer and the other coating portion is developed and remains on the coating to form an image thereon; then

30 (e) depositing a metal-containing material or an ionic material on the surface of the wafer from which the exposed or the unexposed coating portions are removed; then

 (f) removing the exposed or unexposed coating portion from the substrate; and then

 (g) removing the at least one wafer from the IMPD;

 wherein said steps (a) through (f) are performed in an IMPD without the at least one wafer being removed from the IMPD.